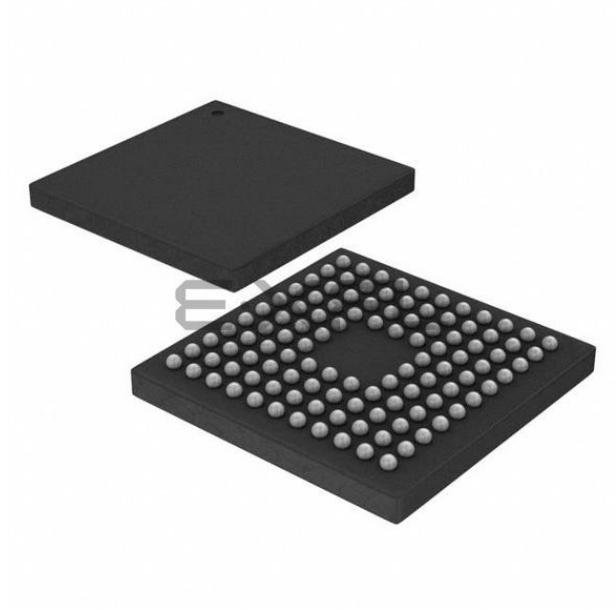

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	90
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	112-BGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg890f1024-bga112t

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32GG microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 µDMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32GG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32GG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32GG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 External Bus Interface (EBI)

The External Bus Interface provides access to external parallel interface devices such as SRAM, FLASH, ADCs and LCDs. The interface is memory mapped into the address bus of the Cortex-M3. This enables seamless access from software without manually manipulating the IO settings each time a read or write is performed. The data and address lines are multiplexed in order to reduce the number of pins required to interface the external devices. The timing is adjustable to meet specifications of the external devices. The interface is limited to asynchronous devices.

2.3 Memory Map

The *EFM32GG890* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32GG890 Memory Map with largest RAM and Flash sizes

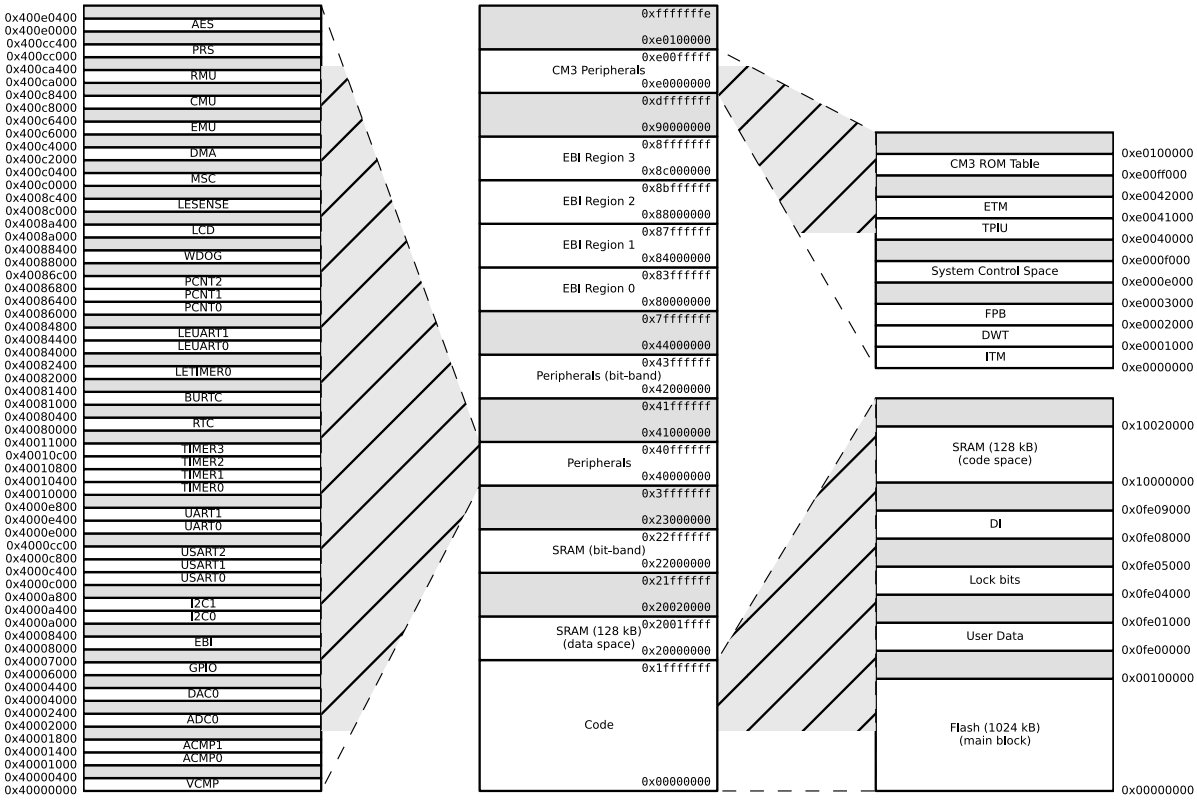


Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.74		1.98	V
$V_{BODintthr-}$	BOD threshold on falling internally regulated supply voltage		1.57		1.70	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85	1.98	V
$V_{PORthr+}$	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF

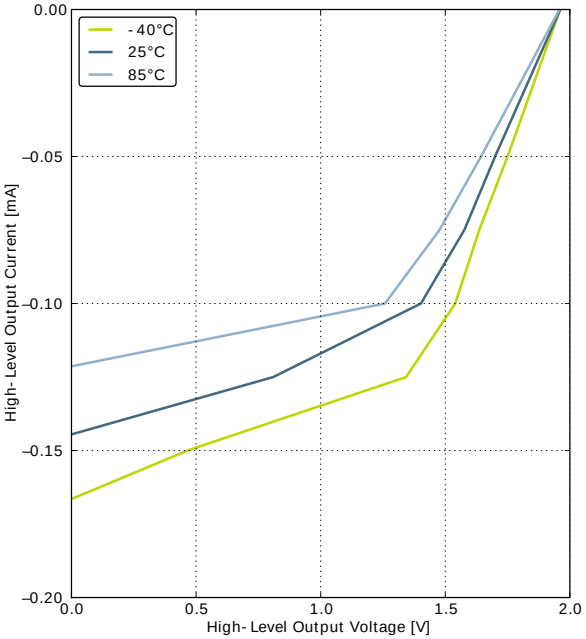
3.7 Flash

Table 3.6. Flash

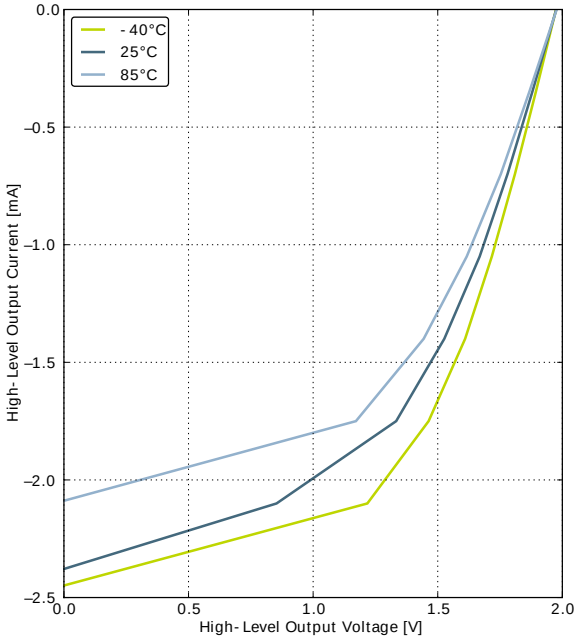
Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{PERASE}	Page erase time	LPERASE == 0	20	20.4	20.8	ms
		LPERASE == 1	40	40.4	40.8	ms
t_{DERASE}	Device erase time				161.6	ms
I_{ERASE}	Erase current	LPERASE == 0			14[1]	mA
		LPERASE == 1			7[1]	mA
I_{WRITE}	Write current	LPWRITE == 0			14[1]	mA
		LPWRITE == 1			7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

[1]Measured at 25°C

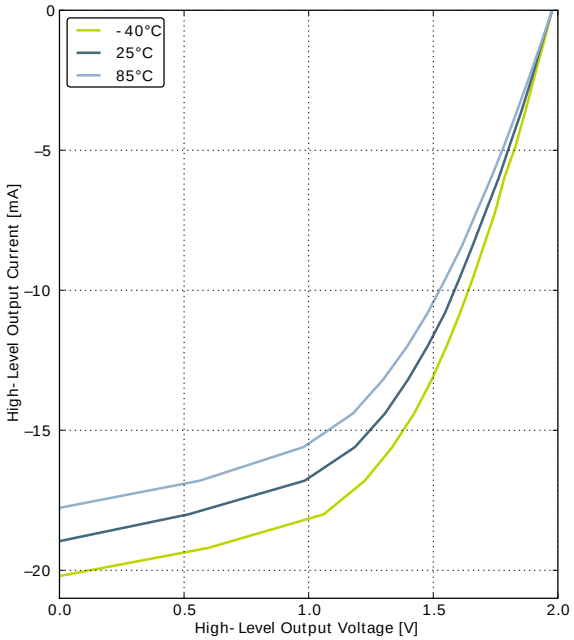
Figure 3.5. Typical High-Level Output Current, 2V Supply Voltage



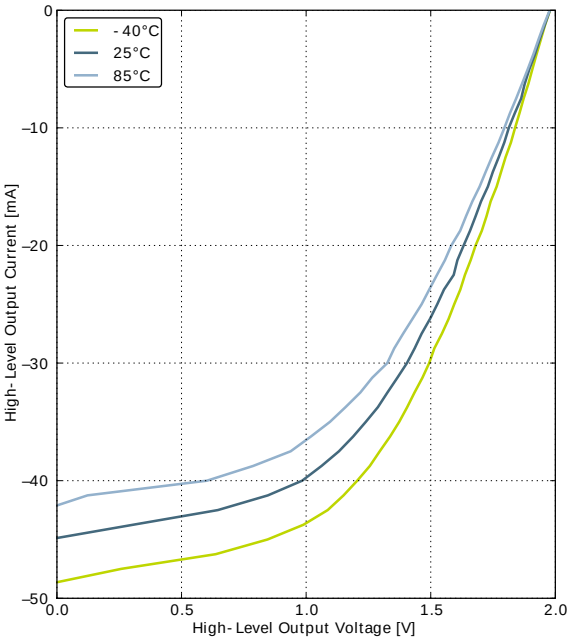
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

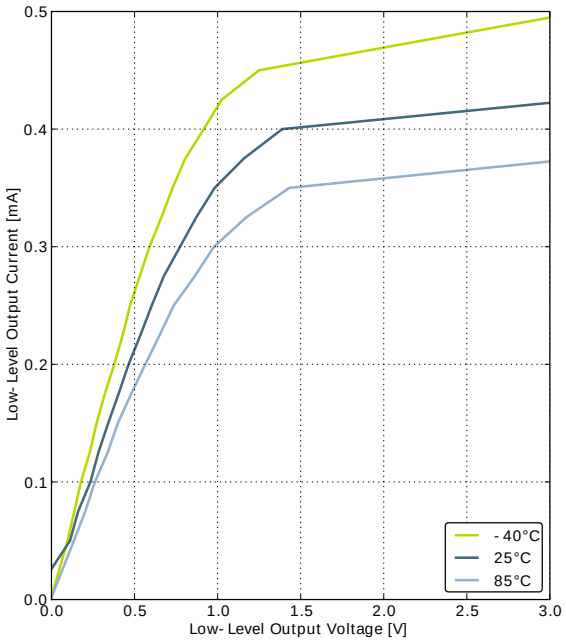


GPIO_Px_CTRL DRIVEMODE = STANDARD

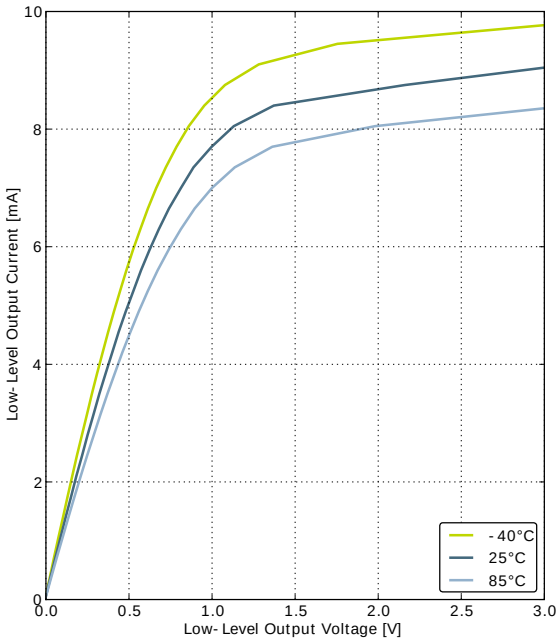


GPIO_Px_CTRL DRIVEMODE = HIGH

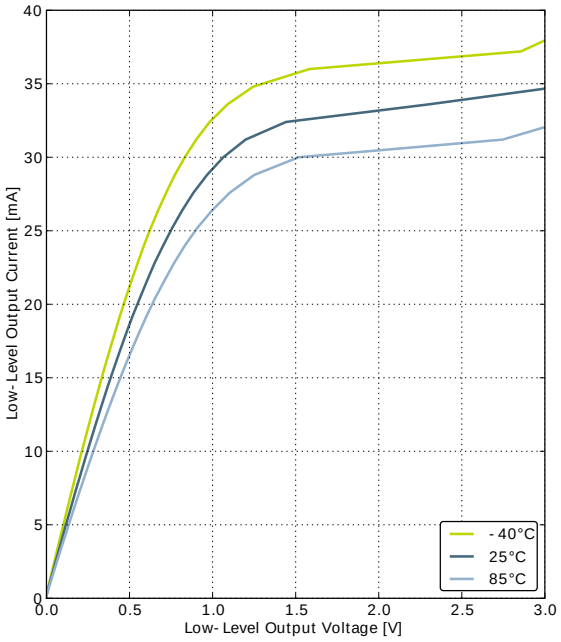
Figure 3.6. Typical Low-Level Output Current, 3V Supply Voltage



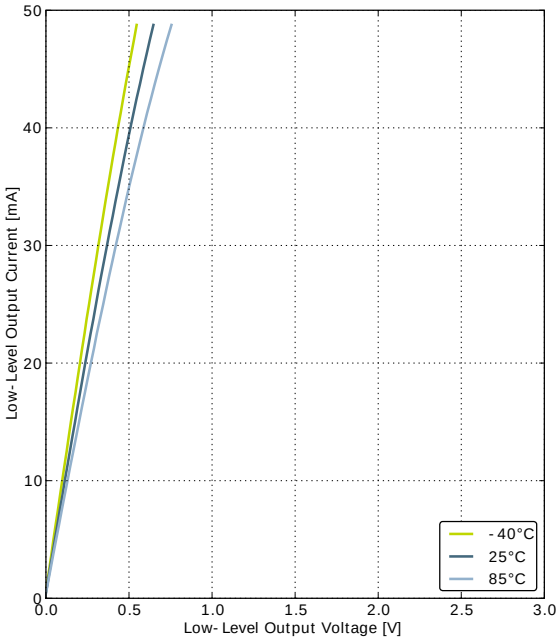
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.13. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

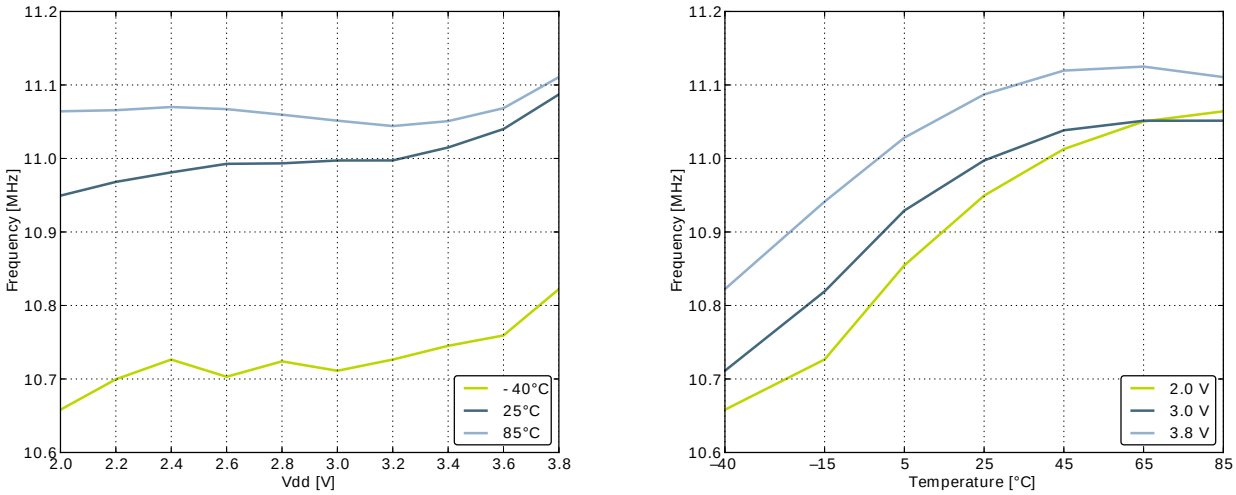


Figure 3.14. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature

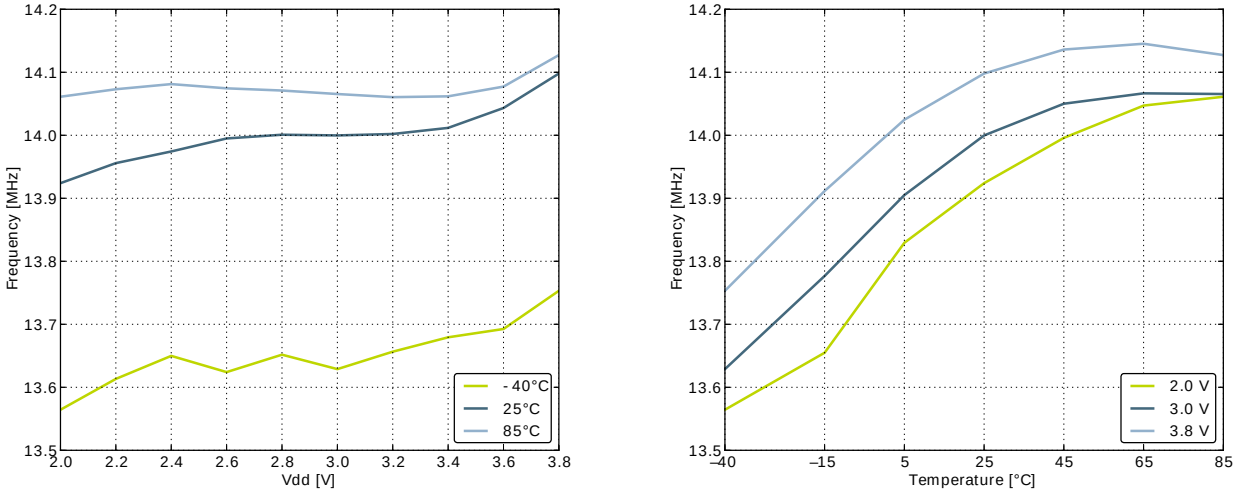
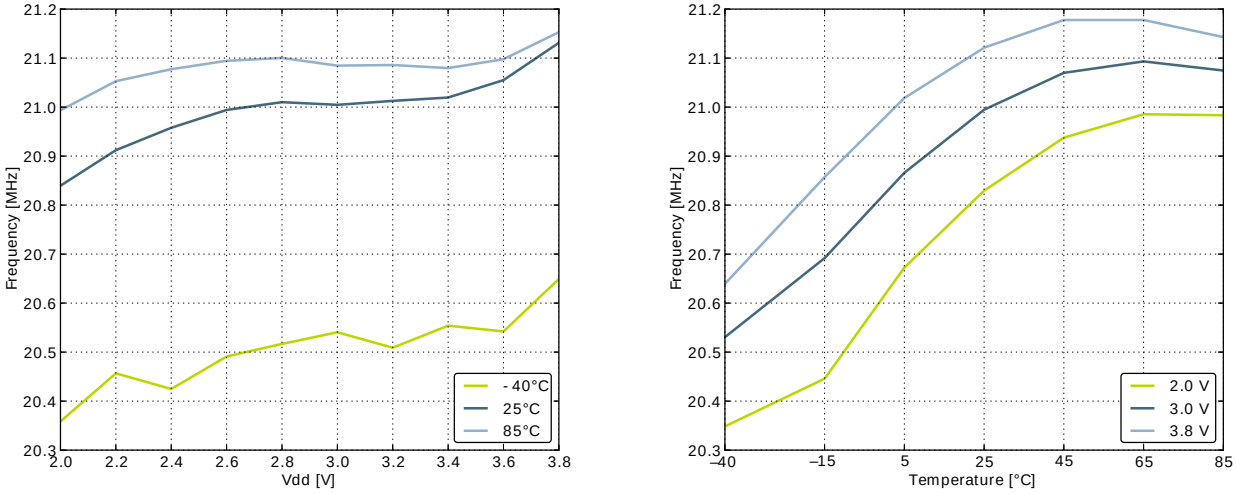


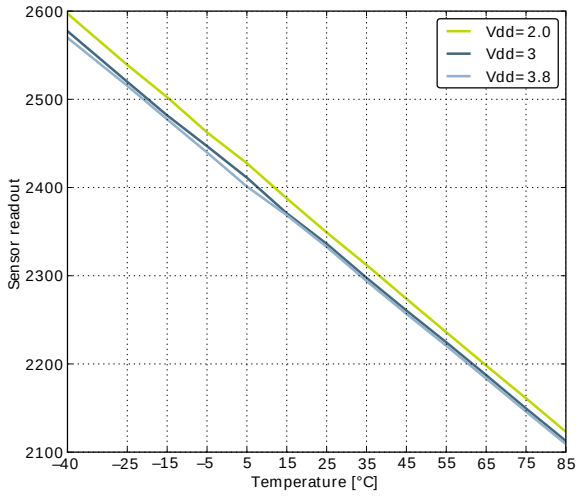
Figure 3.15. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature



Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{ADCIN}	Input capacitance			2		pF
R_{ADCIN}	Input ON resistance		1			MOhm
$R_{ADCFILT}$	Input RC filter resistance			10		kOhm
$C_{ADCFILT}$	Input RC filter/decoupling capacitance			250		fF
f_{ADCCLK}	ADC Clock Frequency				13	MHz
$t_{ADCCONV}$	Conversion time	6 bit	7			ADCCLK Cycles
		8 bit	11			ADCCLK Cycles
		12 bit	13			ADCCLK Cycles
t_{ADCACQ}	Acquisition time	Programmable	1		256	ADCCLK Cycles
$t_{ADCACQVDD3}$	Required acquisition time for VDD/3 reference		2			µs
$t_{ADCSTART}$	Startup time of reference generator and ADC core in NORMAL mode			5		µs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		µs
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		69		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		69		dB
$SFDR_{ADC}$	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		79		dBc
$V_{ADCOFFSET}$	Offset voltage	After calibration, single ended		0.3		mV
		After calibration, differential	-3	0.3	3	mV
$TGRAD_{ADCTH}$	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/°C
DNL_{ADC}	Differential non-linearity (DNL)	V_{DD}= 3.0 V, external 2.5V reference	-1	±0.7	4	LSB
INL_{ADC}	Integral non-linearity (INL), End point method			±1.2	±3.0	LSB
MC_{ADC}	No missing codes		11.999[1]	12		bits

Figure 3.24. ADC Temperature sensor readout



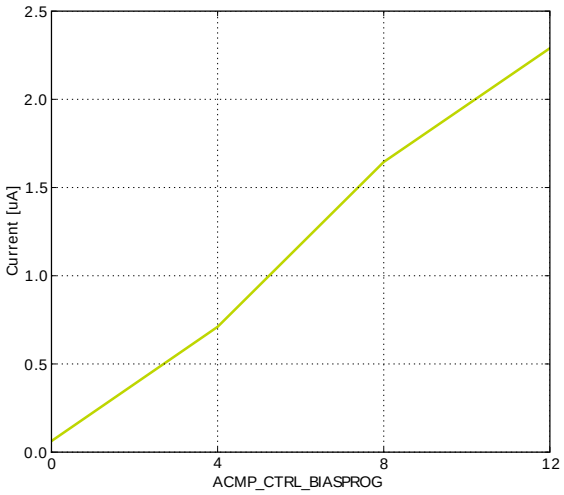
3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

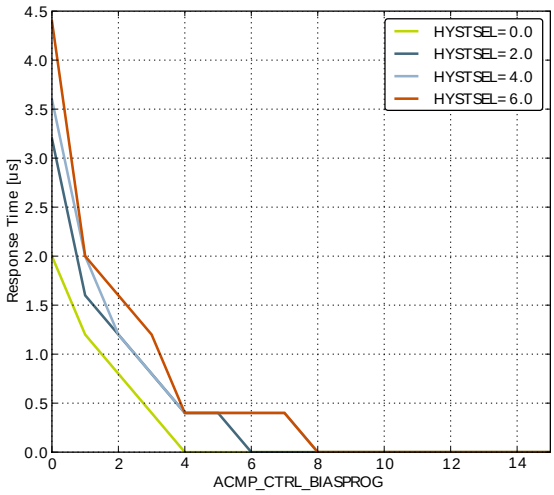
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400[1]	600[1]	µA
		100 kSamples/s, 12 bit		200[1]	260[1]	µA
		1 kSamples/s 12 bit NORMAL		17[1]	25[1]	µA
SR_{DAC}	Sample rate				500	ksamples/s
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cyckles per conversion			2		
$t_{DACCONV}$	Conversion time		2			µs
$t_{DACSETTLE}$	Settling time			5		µs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	17	µA
G_{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW_{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM_{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C_L=75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
R_{INPUT}	Input Resistance			100		Mohm
R_{LOAD}	Load Resistance		200			Ohm
I_{LOAD_DC}	DC Load Current				11	mA
V_{INPUT}	Input Voltage	OPAxHCMDIS=0	V_{SS}		V_{DD}	V
		OPAxHCMDIS=1	V_{SS}		V_{DD}-1.2	V
V_{OUTPUT}	Output Voltage		V_{SS}		V_{DD}	V
V_{OFFSET}	Input Offset Voltage	Unity Gain, V_{SS}<V_{in}<V_{DD}, OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V_{SS}<V_{in}<V_{DD}-1.2, OPAxHCMDIS=1		1		mV
V_{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR_{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/µs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/µs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/µs
N_{OPAMP}	Voltage Noise	V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=0		101		$µV_{RMS}$
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=1		141		$µV_{RMS}$

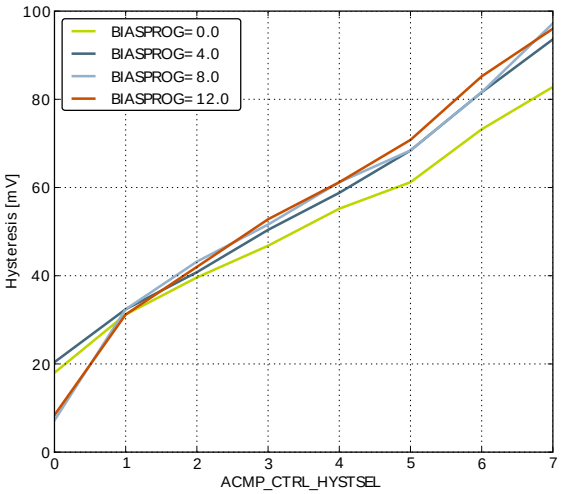
Figure 3.30. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4



Response time



Hysteresis

Table 3.19. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_WEn} [1 2 3 4]	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-6.00 + (WRHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_WEn} [1 2 3 4 5]	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	-14.00 + (WRSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_WEn} [1 2 3 4 5]	EBI_WEn/EBI_NANDWEn pulse width	-7.00 + ((WRSTRB +1) * $t_{HFCORECLK}$)			ns

[1]Applies for all addressing modes (figure only shows D16 addressing mode)
[2]Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)
[3]Applies for all polarities (figure only shows active low signals)
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)
[5] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by 1/2 * $t_{HFCLKNODIV}$.

Figure 3.32. EBI Address Latch Enable Related Output Timing

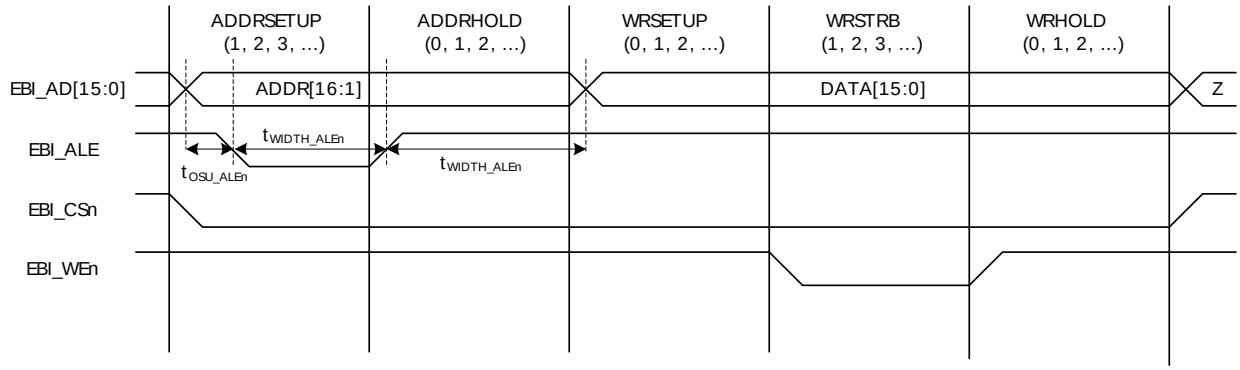


Table 3.20. EBI Address Latch Enable Related Output Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_ALEn} [1 2 3 4]	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	-6.00 + (ADDRHOLD[5] * $t_{HFCORECLK}$)			ns
t_{OSU_ALEn} [1 2 4]	Output setup time, from EBI_AD valid to leading EBI_ALE edge	-13.00 + (0 * $t_{HFCORECLK}$)			ns
t_{WIDTH_ALEn} [1 2 3 4]	EBI_ALEn pulse width	-7.00 + (ADDRSETUP+1) * $t_{HFCORECLK}$)			ns

[1]Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)
[2]Applies for all polarities (figure only shows active low signals)
[3] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of tOH_ALEn by $t_{HFCORECLK}$ - 1/2 * $t_{HFCLKNODIV}$.
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)
[5]Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

Figure 3.34. EBI Read Enable Related Timing Requirements

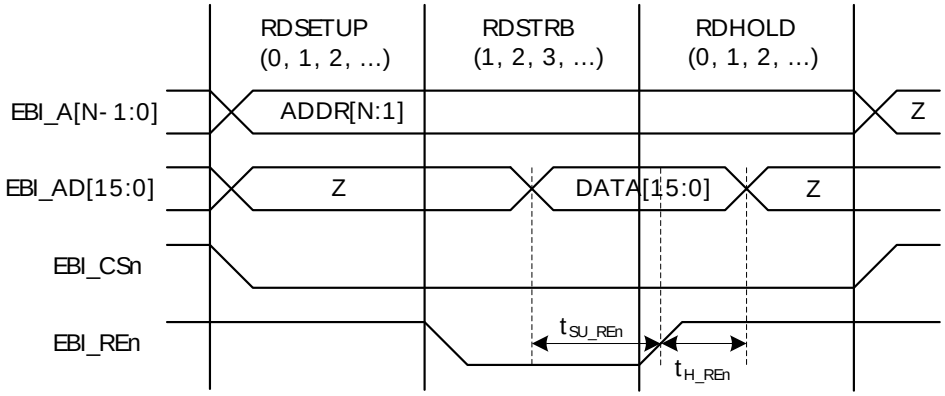


Table 3.22. EBI Read Enable Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_REn} [1 2 3 4]	Setup time, from EBI_AD valid to trailing EBI_REn edge	37			ns
t_{H_Ren} [1 2 3 4]	Hold time, from trailing EBI_REn edge to EBI_AD invalid	-1			ns

[1]Applies for all addressing modes (figure only shows D16A8).
[2]Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)
[3]Applies for all polarities (figure only shows active low signals)
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

Figure 3.35. EBI Ready/Wait Related Timing Requirements

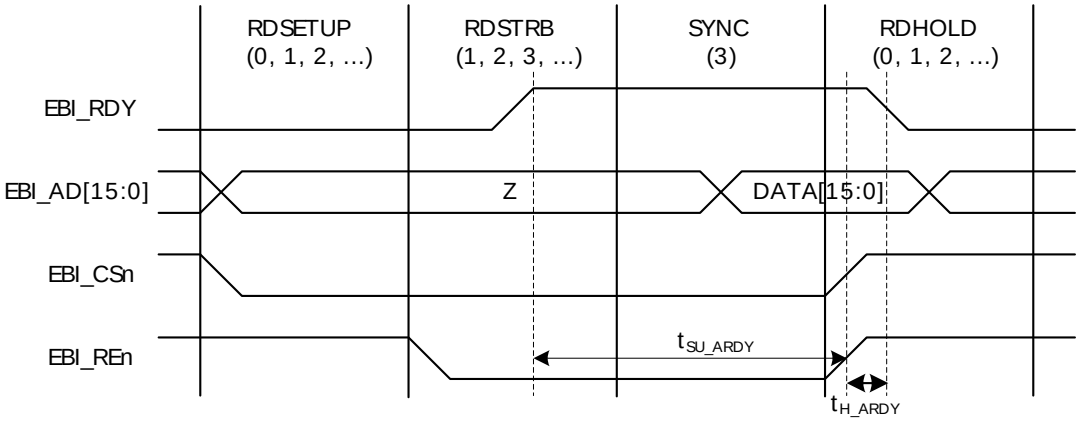


Table 3.23. EBI Ready/Wait Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_ARDY} [1 2 3 4]	Setup time, from EBI_ARDY valid to trailing EBI_REn, EBI_WEn edge	37 + (3 * $t_{HFCORECLK}$)			ns

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
LCD_SEG9	PE13							LCD segment line 9. Segments 8, 9, 10 and 11 are controlled by SEGEN2.
LCD_SEG10	PE14							LCD segment line 10. Segments 8, 9, 10 and 11 are controlled by SEGEN2.
LCD_SEG11	PE15							LCD segment line 11. Segments 8, 9, 10 and 11 are controlled by SEGEN2.
LCD_SEG12	PA15							LCD segment line 12. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG13	PA0							LCD segment line 13. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG14	PA1							LCD segment line 14. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG15	PA2							LCD segment line 15. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG16	PA3							LCD segment line 16. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG17	PA4							LCD segment line 17. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG18	PA5							LCD segment line 18. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG19	PA6							LCD segment line 19. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG20/ LCD_COM4	PB3							LCD segment line 20. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 4
LCD_SEG21/ LCD_COM5	PB4							LCD segment line 21. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 5
LCD_SEG22/ LCD_COM6	PB5							LCD segment line 22. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 6
LCD_SEG23/ LCD_COM7	PB6							LCD segment line 23. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 7
LCD_SEG24	PF6							LCD segment line 24. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG25	PF7							LCD segment line 25. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG26	PF8							LCD segment line 26. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG27	PF9							LCD segment line 27. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG28	PD9							LCD segment line 28. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG29	PD10							LCD segment line 29. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG30	PD11							LCD segment line 30. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG31	PD12							LCD segment line 31. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG32	PB0							LCD segment line 32. Segments 32, 33, 34 and 35 are controlled by SEGEN8.
LCD_SEG33	PB1							LCD segment line 33. Segments 32, 33, 34 and 35 are controlled by SEGEN8.
LCD_SEG34	PB2							LCD segment line 34. Segments 32, 33, 34 and 35 are controlled by SEGEN8.

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. BGA112 PCB Land Pattern

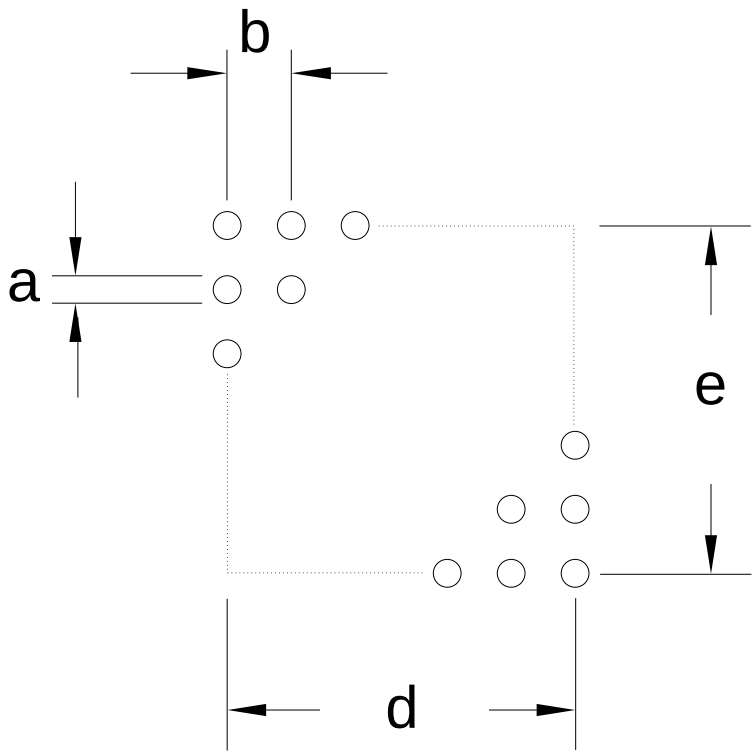


Table 5.1. BGA112 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.35
b	0.80
d	8.00
e	8.00

Figure 5.3. BGA112 PCB Stencil Design

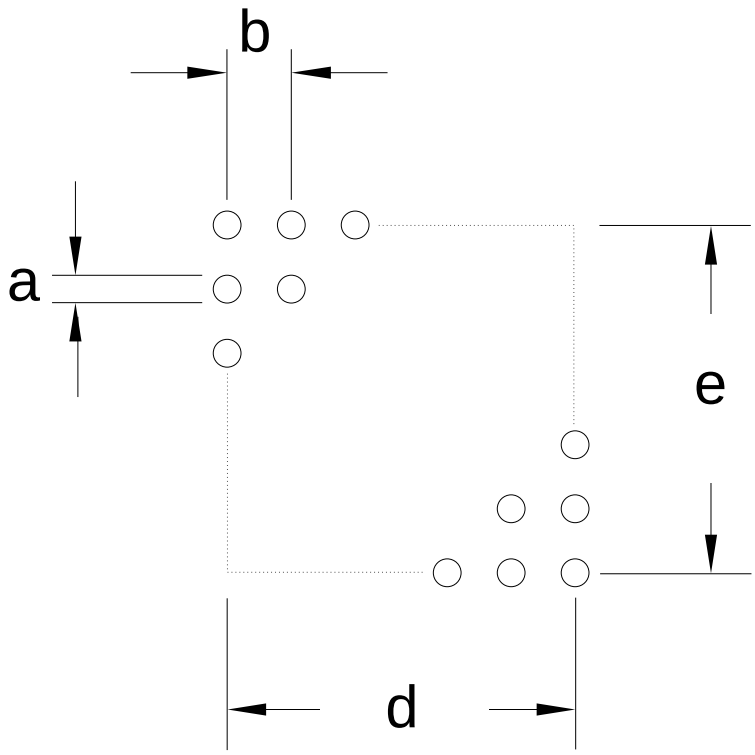


Table 5.3. BGA112 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.33
b	0.80
d	8.00
e	8.00

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 67) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

7.10 Revision 0.91

March 21th, 2011

Added new alternative locations for EBI and SWO.

Corrected slew rate data for Opamps.

7.11 Revision 0.90

February 4th, 2011

Initial preliminary release.

B Contact Information

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Please visit the Silicon Labs Technical Support web page:
http://www.silabs.com/support/pages/contacttechnicalsupport.aspx
and register to submit a technical support request.

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